

L Number	Hits	Search Text	DB	Time stamp
-	0	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same (plasma adj flood adj gun)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 11:55
-	237	(depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:20
-	4068	((depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) (wafer adj fabrication)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:21
-	30	((depolarization or (charge adj reduct?\$5) or (electrostatic adj discharge) or (electrostatic adj depolarization)) same plasma) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:25
-	79	depolarization adj (method or process)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:25
-	90	((charge adj reduct?\$5) or depolarization) adj (method or process)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:26
-	0	((charge adj reduct?\$5) or depolarization) adj (method or process) and (expos?\$5 with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:27
-	11	((charge adj reduct?\$5) or depolarization) adj (method or process) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 10:27
-	7553	(depolarization or (de adj polarization))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:03
-	6	((depolarization or (de adj polarization))) and (wafer adj fabricat?\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 11:58
-	12	((electrostatic adj discharge) or esd) with (wafer adj fabricat?\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:02
-	0	(polarization adj charge?) with (wafer adj fabricat?\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:03
-	1	(depolarization or (de adj polarization)) with (wafer adj fabricat?\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:05
-	0	depolarization with (wafer near2 pad)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:08

-	37	semiconductor adj fabrication adj tool?	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:08
-	0	(semiconductor adj fabrication adj tool?) with (discharge near2 electrostatic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:10
-	0	(semiconductor adj fabrication adj tool?) with ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:10
-	0	(semiconductor adj fabrication adj tool?) same ((discharge near2 electrostatic) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:11
-	207	(ion adj implantation) same ((electrostatic adj charge) or esd or (electrostatic adj discharge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:12
-	41	((ion adj implantation) same ((electrostatic adj charge) or esd or (electrostatic adj discharge))) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:12
-	1	(wafer near2 pad) with (depolarization or (de adj polarization) or (electrostatic adj discharge) or esd or (charge near2 (reduct?5 or neutralization)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 12:45
-	4	((("5089710") or ("5399871"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 13:25
-	0	("(insulating near2 pad) with plasma").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:36
-	14	(insulating near2 pad) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:38
-	118741	(H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39
-	23297	((H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39
-	3	((H01L021/3065 or H01L021/205 or H01L021/31 or H01L021/68).ipc.) and plasma) and (insulating near3 pad?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/27 14:39
-	1381	depolarization and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:18

-	3	depolarization and (exposing near5 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:19
-	0	depolarization near10 (fabrication with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:20
-	5	depolarization and (fabrication with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:22
-	181	((depolariz\$5 or neutraliz\$5) and (fabrication with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:27
-	59258	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:28
-	6779	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) and plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:28
-	758	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near10 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:28
-	2	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 (fabrication near5 plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/19 09:29
-	612	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:16
-	302	((depolariz\$5 or neutraliz\$5 or reduc\$5) near5 (charge or electrostatic)) near5 plasma) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:15
-	36283	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:53
-	5804	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma) and fabrication	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:18
-	7713	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma) and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:20
-	3067	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma) and electrostatic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:28

-	436	((depolariz\$5 or neutraliz\$5 or reduc\$5) with plasma) and misalignment	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:34
-	77	plasma with (electrostatic adj charge?)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:50
-	2	5399871.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:50
-	74658	(depolariz\$5 or neutraliz\$5 or reduc\$5 or discharg\$5) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:54
-	306	(electrostatic near5 (depolariz\$5 or neutraliz\$5 or reduc\$5 or discharg\$5)) with plasma	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/20 13:55
-	2	ep-709877-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/13 08:48